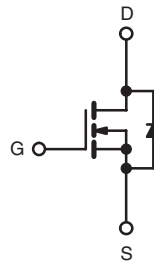
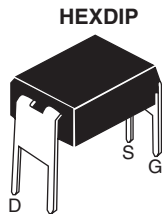


Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω)	$V_{GS} = 5.0$ V 0.10
Q_g (Max.) (nC)	18
Q_{gs} (nC)	4.5
Q_{gd} (nC)	12
Configuration	Single



N-Channel MOSFET

FEATURES

- Dynamic dV/dt Rating
- For Automatic Insertion
- End Stackable
- Logic-Level Gate Drive
- $R_{DS(on)}$ Specified at $V_{GS} = 4$ V and 5 V
- 175 °C Operating Temperature
- Fast Switching
- Lead (Pb)-free Available


 Available
RoHS*
 COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The 4 pin DIP package is a low cost machine-insertible case style which can be stacked in multiple combinations on standard 0.1" pin centers. The dual drain servers as a thermal link to the mounting surface for power dissipation levels up to 1 W.



ORDERING INFORMATION	
Package	HEXDIP
Lead (Pb)-free	IRLD024PbF
	SiHLD024-E3
SnPb	IRLD024
	SiHLD024

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 10	
Continuous Drain Current	I_D	$T_C = 25$ °C	2.5
		$T_C = 100$ °C	1.8
Pulsed Drain Current ^a	I_{DM}	20	A
Linear Derating Factor		0.0083	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	91	mJ
Maximum Power Dissipation	P_D	1.3	W
Peak Diode Recovery dV/dt^c	dV/dt	4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$ V, starting $T_J = 25$ °C, $L = 16$ mH, $R_G = 25$ Ω , $I_{AS} = 2.5$ A (see fig. 12).
- $I_{SD} \leq 17$ A, $dI/dt \leq 140$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	TYP.	MAX.	UNIT			
Maximum Junction-to-Ambient	R_{thJA}	-	120	°C/W			
SPECIFICATIONS $T_J = 25\text{ °C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	60	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C , $I_D = 1\text{ mA}$	-	0.060	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1.0	-	2.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 10\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA	
		$V_{DS} = 48\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ °C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 5.0\text{ V}$	-	-	0.10	Ω	
		$V_{GS} = 4.0\text{ V}$	-	-	0.14		
Forward Transconductance	g_{fs}	$V_{DS} = 25\text{ V}$, $I_D = 1.5\text{ A}^b$	3.7	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1.0\text{ MHz}$, see fig. 5	-	870	-	pF	
Output Capacitance	C_{oss}		-	360	-		
Reverse Transfer Capacitance	C_{rss}		-	53	-		
Total Gate Charge	Q_g	$V_{GS} = 5.0\text{ V}$	$I_D = 17\text{ A}$, $V_{DS} = 48\text{ V}$ see fig. 6 and 13 ^b	-	-	18	nC
Gate-Source Charge	Q_{gs}			-	-	4.5	
Gate-Drain Charge	Q_{gd}			-	-	12	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $I_D = 17\text{ A}$ $R_G = 9.0\text{ }\Omega$, $R_D = 1.7\text{ }\Omega$, see fig. 10 ^b	-	11	-	ns	
Rise Time	t_r		-	110	-		
Turn-Off Delay Time	$t_{d(off)}$		-	23	-		
Fall Time	t_f		-	41	-		
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.0	-	nH
Internal Source Inductance	L_S			-	6.0	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	2.5	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	20	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ °C}$, $I_S = 2.5\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ °C}$, $I_F = 17\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	110	260	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.49	1.5	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

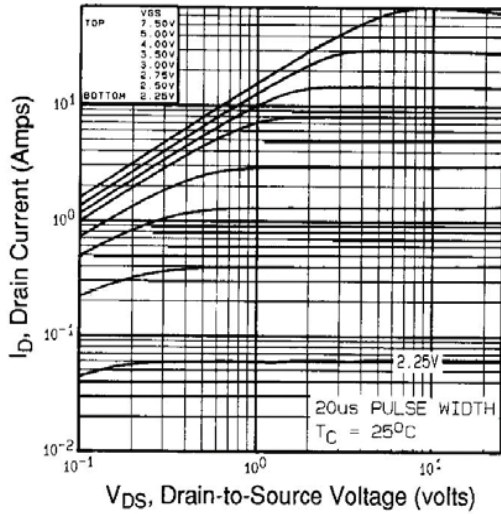


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

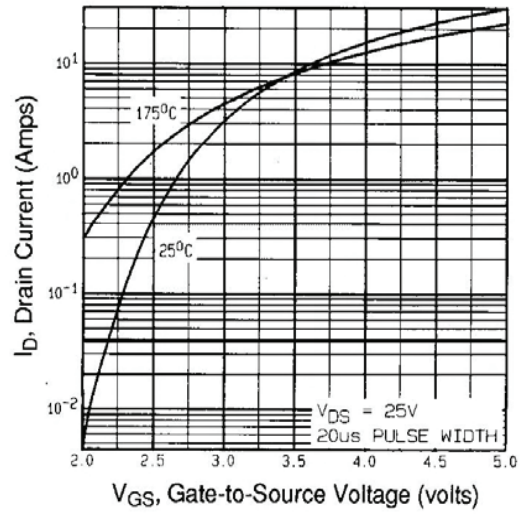


Fig. 3 - Typical Transfer Characteristics

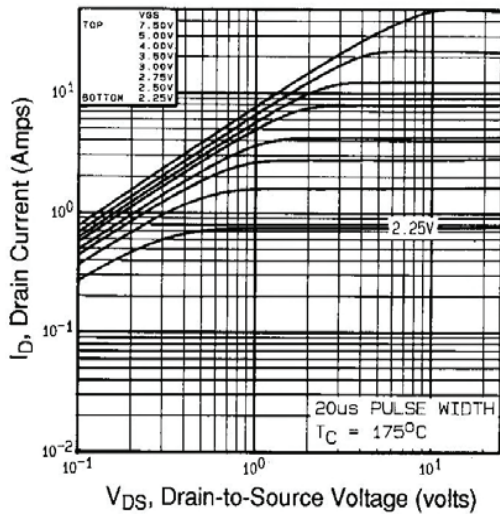


Fig. 2 - Typical Output Characteristics, $T_C = 175\text{ }^\circ\text{C}$

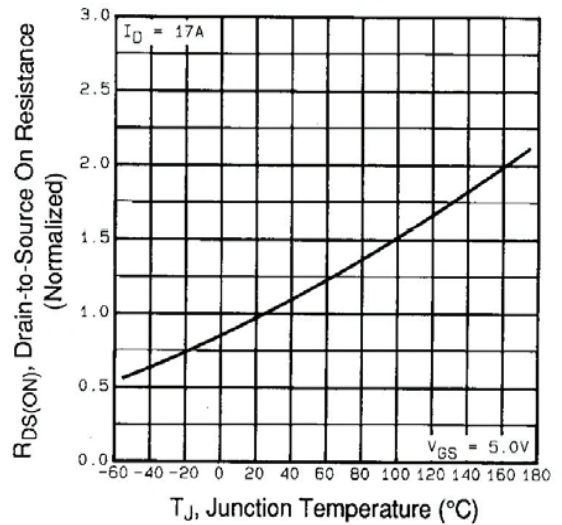


Fig. 4 - Normalized On-Resistance vs. Temperature

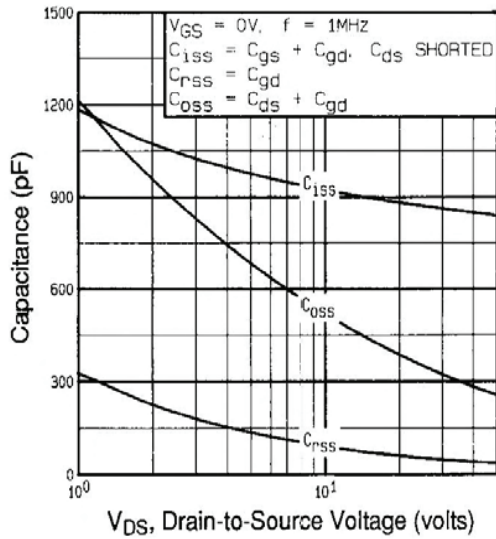


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

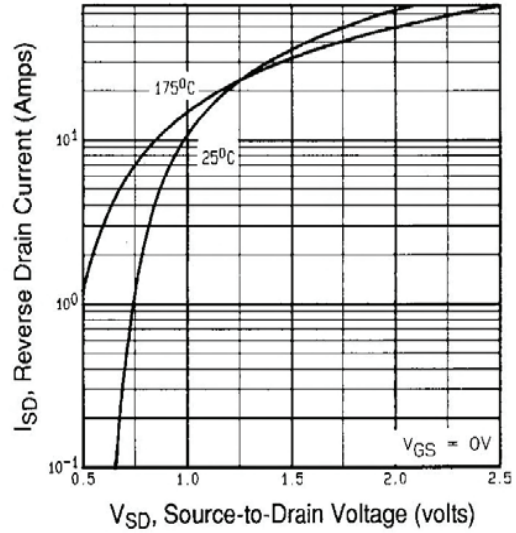


Fig. 7 - Typical Source-Drain Diode Forward Voltage

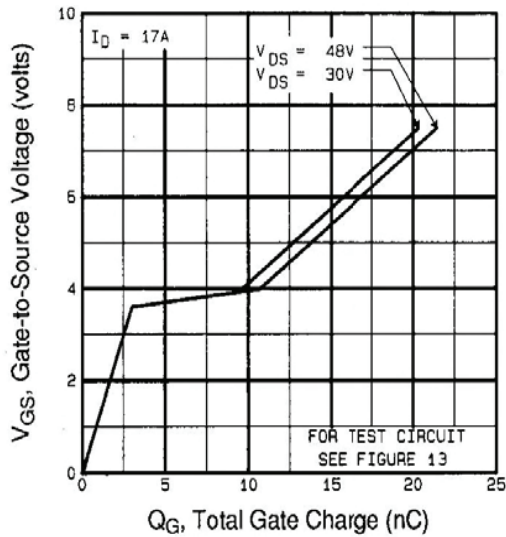


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

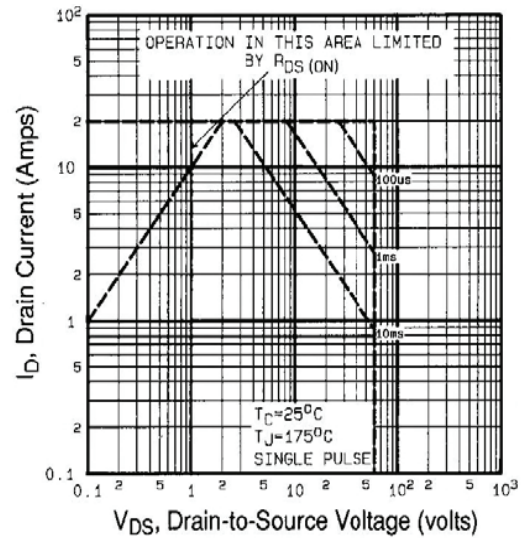


Fig. 8 - Maximum Safe Operating Area

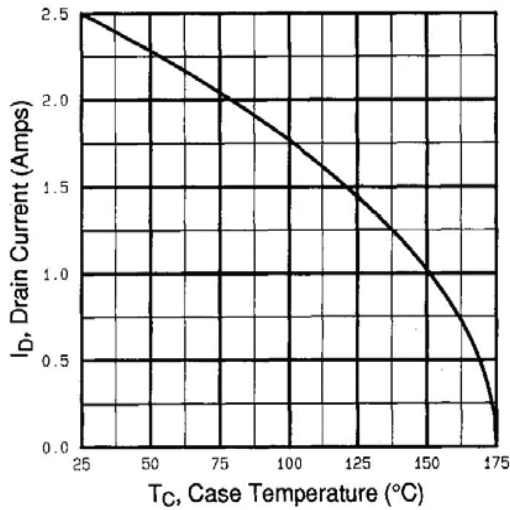


Fig. 9 - Maximum Drain Current vs. Case Temperature

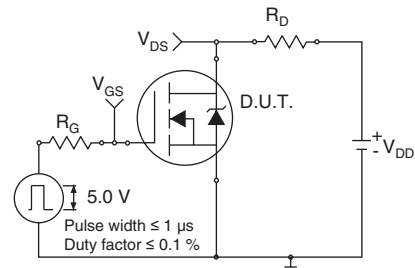


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

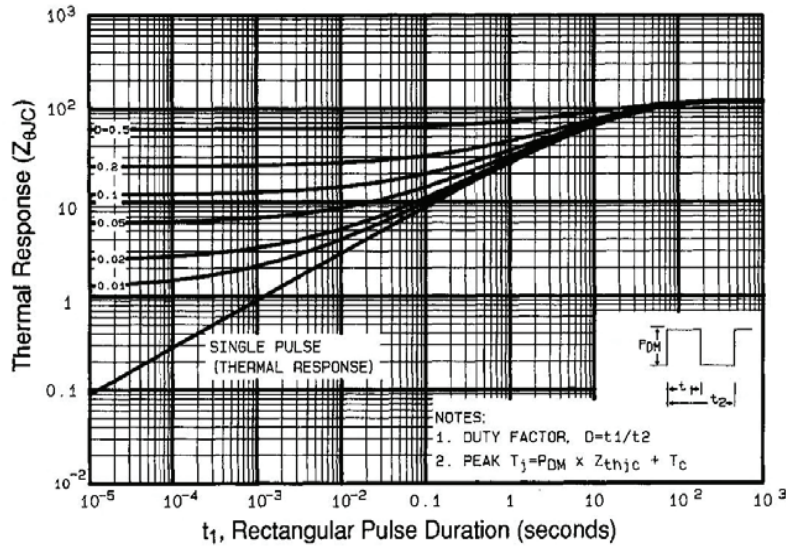


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

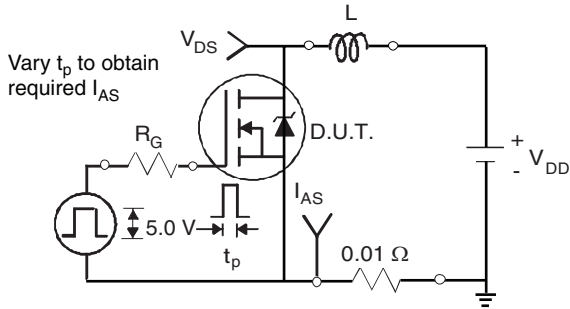


Fig. 12a - Unclamped Inductive Test Circuit

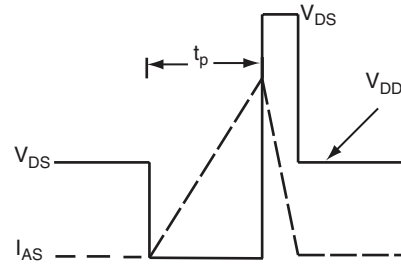


Fig. 12b - Unclamped Inductive Waveforms

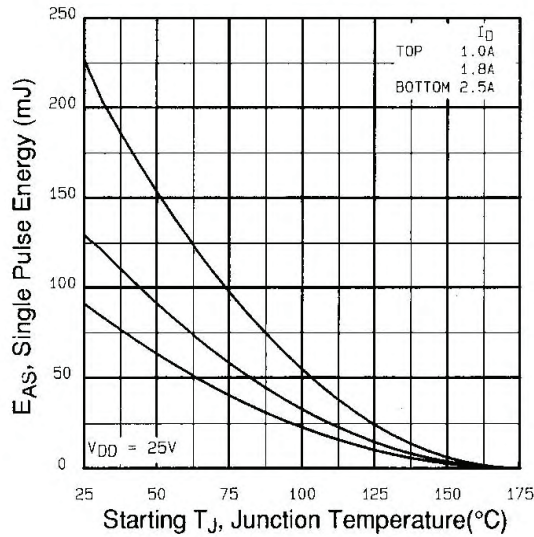


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

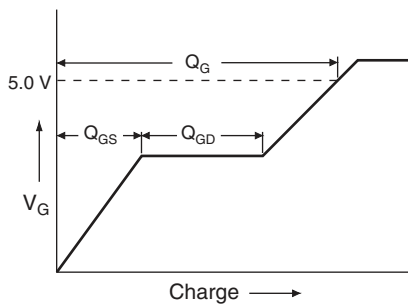


Fig. 13a - Basic Gate Charge Waveform

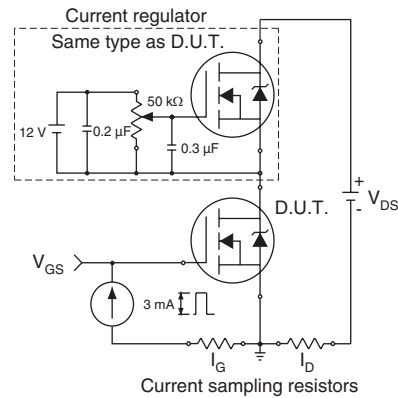
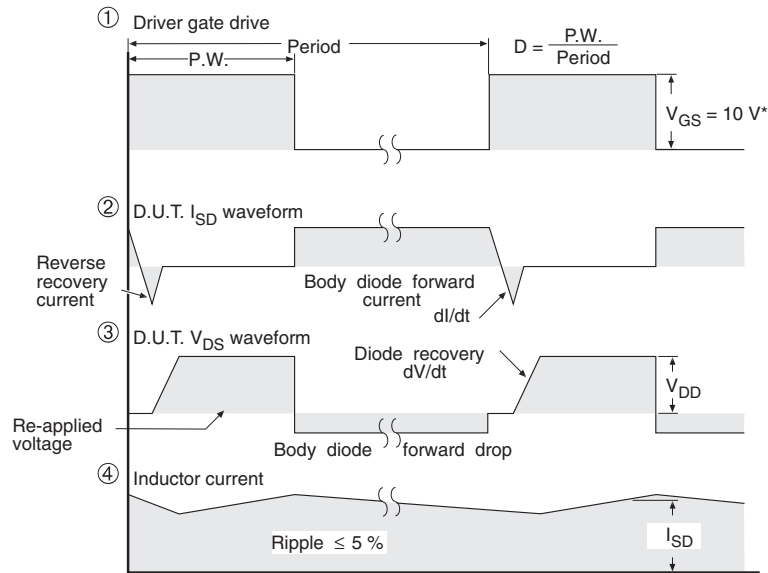
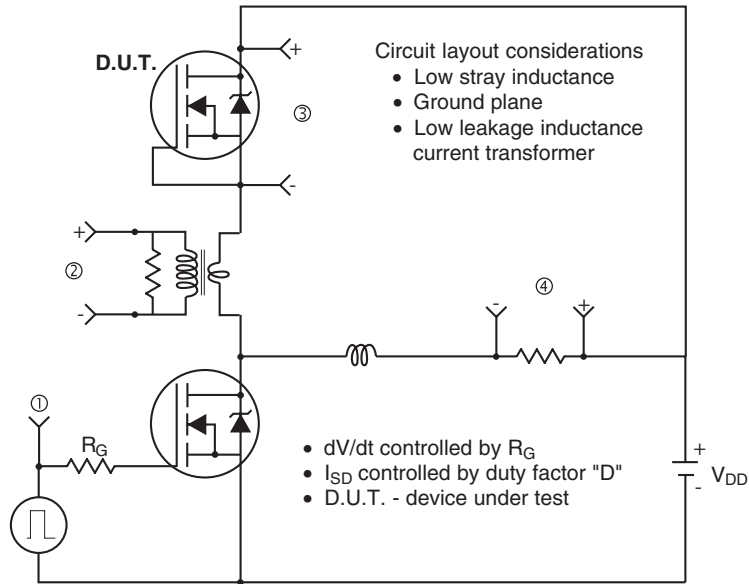


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit


* $V_{GS} = 5V$ for logic level devices and $3V$ drive devices

Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?91308>.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.